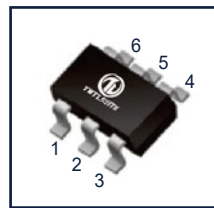
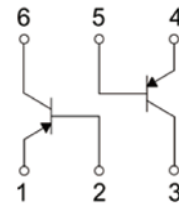


Features

- Epitaxial planar die construction
- Ideal for low power amplification and switching



SOT-363



Equivalent Circuit

Absolute Maximum Ratings(T_A=25℃)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-0.2	A
P _C	Collector Power Dissipation	0.2	W
R _{θJA}	Thermal Resistance, Junction to Ambient Air	625	℃/W
T _J , T _{stg}	Operation Junction And Storage Temperature Range	-55 ~ +150	℃

Electrical Characteristics (T_A=25℃ unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-10μA, I _E =0	-40			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA, I _B =0	-40			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-10μA, I _C =0	-5			V
I _{CEX}	Collector cut-off current	V _{CE} =-30V, V _{EB(off)} =-3V			-50	nA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V, I _C =0			-50	nA
h _{FE(1)}	DC current gain	V _{CE} =-1V, I _C =-0.1mA	60			
h _{FE(2)}		V _{CE} =-1V, I _C =-1mA	80			
h _{FE(3)}		V _{CE} =-1V, I _C =-10mA	100		300	
h _{FE(4)}		V _{CE} =-1V, I _C =-50mA	60			
h _{FE(5)}		V _{CE} =-1V, I _C =-100mA	30			
V _{CE(sat)(1)}	Collector-emitter saturation voltage	I _C =-10mA, I _B =-1mA			-0.25	V
V _{CE(sat)(2)}		I _C =-50mA, I _B =-5mA			-0.4	V
V _{BE(1)}	Base-emitter voltage	I _C =-10mA, I _B =-1mA	-0.65		-0.85	V
V _{BE(2)}		I _C =-50mA, I _B =-5mA			-0.95	V
f _T	Transition frequency	V _{CE} =-20V, I _C =-10mA, f=100MHz	250			MHz
C _{ob}	Output Capacitance	V _{CB} =-5V, I _E =0A, f=1MHz			4.5	pF
NF	Noise figure	V _{CE} =-5V, I _C =-0.1mA, f=1KHz, R _G =1KΩ			4	dB
t _d	Delay time	V _{CC} =-3V, V _{BE} =0.5V I _C =-10mA, I _{B1} =-I _{B2} =-1mA			35	nS
t _r	Rise time				35	nS
t _s	Storage time				225	nS
t _f	Fall time	V _{CC} =-3V, I _C =-10mA I _{B1} =-I _{B2} =-1mA			75	nS

Ordering information

Product ID	Pack	Naming rule	Marking	hFE(1)	Qty(PCS)
MMDT3906	SOT-363	MMDT3906 产品名称 product name	K3N	100-300	3000

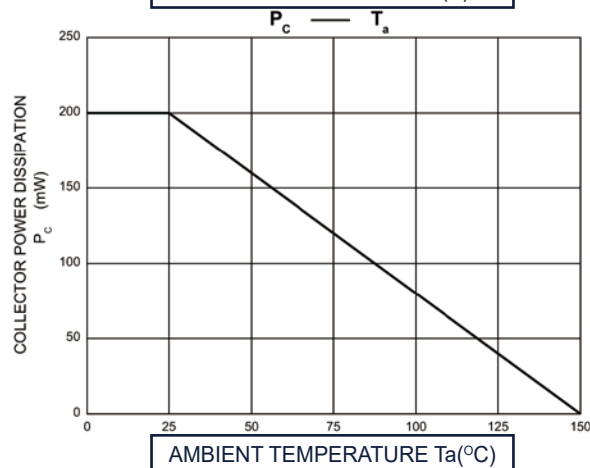
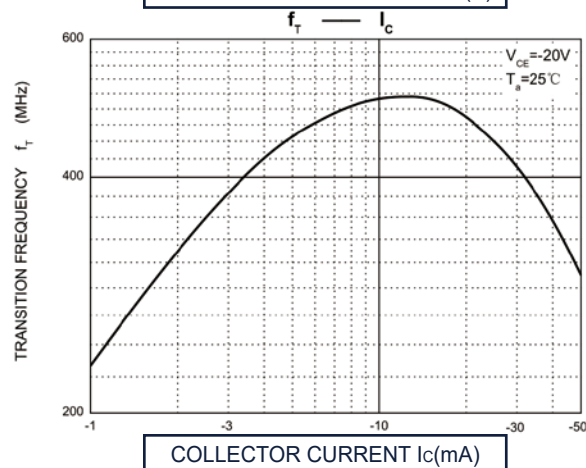
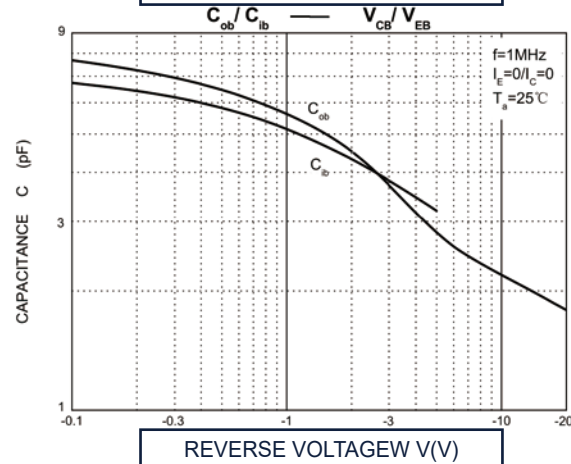
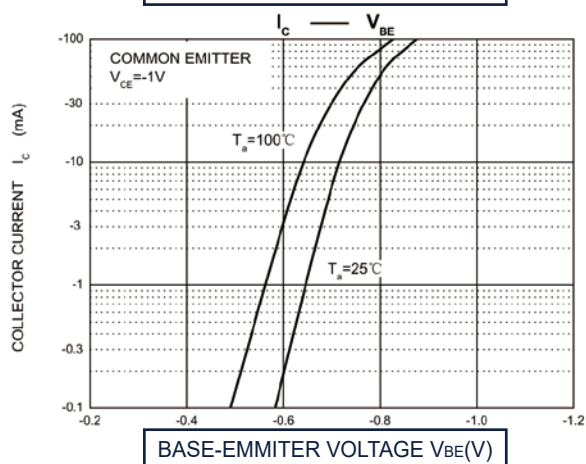
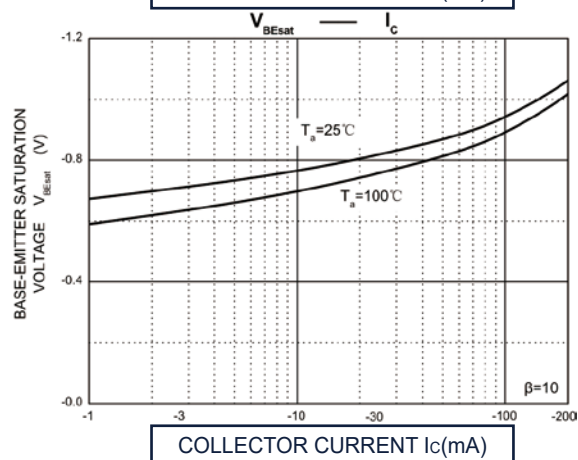
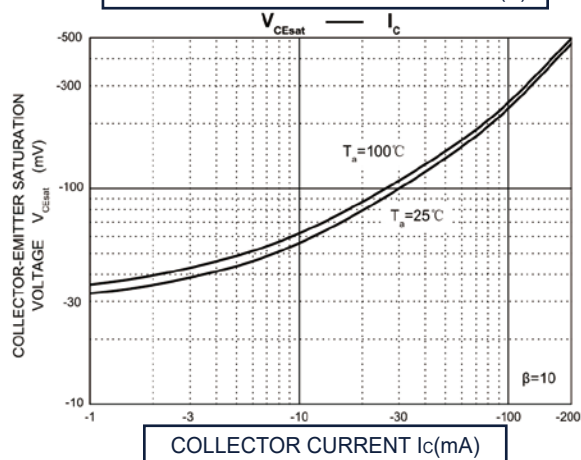
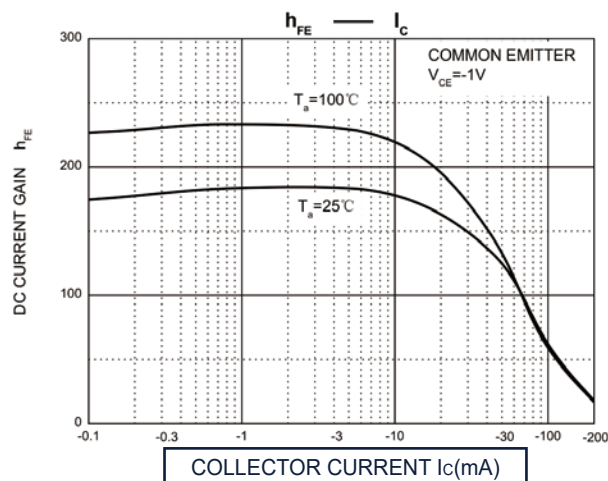
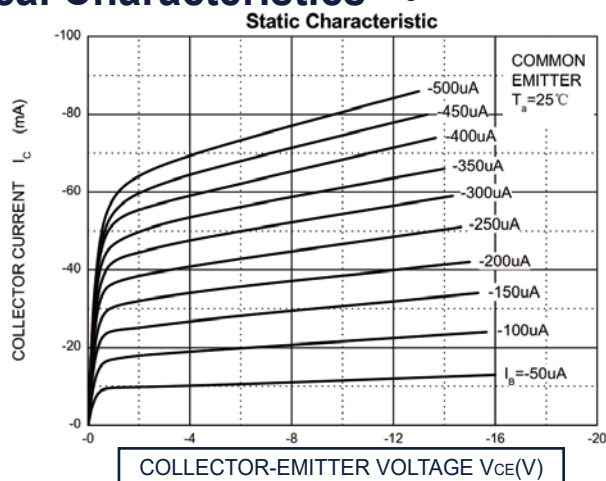


TWTLSEMI

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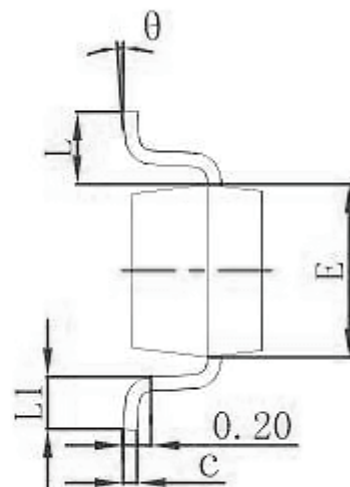
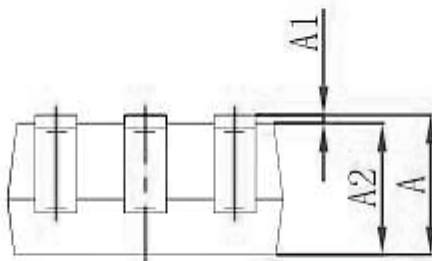
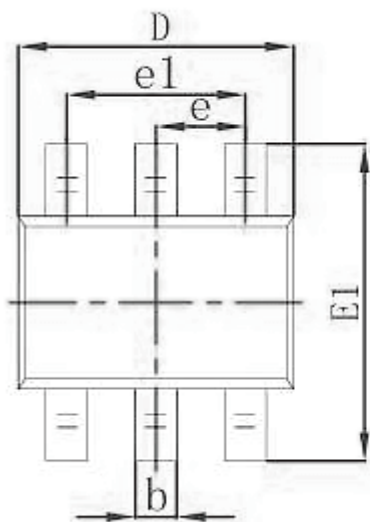
SOT-363 DUAL TRANSISTOR (PNP+PNP)

Typical Characteristics





SOT-363 Package Outline Dimensions



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°